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APPLICATION NO. FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/707,703 01/06/2004		Sheng-Tai Young	FTCP0030USA 1702	
27765	7590 05/18/2005	EXAMINER		
NORTH AMERICA INTERNATIONAL PATENT OFFICE (NAIPC)			ERDEM, FAZLI	
	P.O. BOX 506 MERRIFIELD, VA 22116			PAPER NUMBER
			2826	
			DATE MAILED: 05/18/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

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		Application No.	Applicant(s)			
Office Action Summary		10/707,703	YOUNG ET AL.			
		Examiner	Art Unit			
		Fazli Erdem	2826			
The MAILING DATE Period for Reply	E of this communication app	ears on the cover sheet with the c	orrespondence address			
THE MAILING DATE OF - Extensions of time may be availat after SIX (6) MONTHS from the m - If the period for reply specified ab - If NO period for reply is specified - Failure to reply within the set or ex	THIS COMMUNICATION. ble under the provisions of 37 CFR 1.13 ailing date of this communication. bove is less than thirty (30) days, a reply above, the maximum statutory period w kended period for reply will, by statute, ater than three months after the mailing	IS SET TO EXPIRE 3 MONTH(66(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) days ill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONEI date of this communication, even if timely filed	nely filed s will be considered timely. the mailing date of this communication. O (35 U.S.C. § 133).			
Status						
1) Responsive to com	munication(s) filed on 23 Fe	bruary 2005.				
2a) This action is FINA	This action is FINAL . 2b) ☐ This action is non-final.					
	Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.					
Disposition of Claims			,			
4)⊠ Claim(s) <u>1-11</u> is/are pending in the application. 4a) Of the above claim(s) is/are withdrawn from consideration. 5)⊠ Claim(s) <u>6-11</u> is/are allowed.						
6)⊠ Claim(s) <u>1-4</u> is/are in 7)⊠ Claim(s) <u>5</u> is/are ob 8)□ Claim(s) are	-	election requirement.	•			
Application Papers			•			
9) The specification is	objected to by the Examiner	r.				
10) The drawing(s) filed	0)☐ The drawing(s) filed on is/are: a)☐ accepted or b)☐ objected to by the Examiner.					
Applicant may not req	uest that any objection to the o	frawing(s) be held in abeyance. See	e 37 CFR 1.85(a).			
<u> </u>	Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d). The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.					
Priority under 35 U.S.C. § 1	19					
a) All b) Some * 1. Certified copi 2. Certified copi 3. Copies of the application from	c) None of: es of the priority documents es of the priority documents certified copies of the prior om the International Bureau	s have been received in Application ity documents have been received	on No ed in this National Stage			
Attachment(s)	,					
Aπacnmenτ(s) 1) Notice of References Cited (P	TO-892)	4) 🔲 Interview Summary	(PTO-413)			
2) D Notice of Draftsperson's Pater		Paper No(s)/Mail Da				

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DETAILED ACTION

Response to Arguments

Applicant's arguments filed 02/23/2005 have been fully considered but they are not

persuasive. Goo discloses a method of fabricating a nonvolatile semiconductor memory device

where in Fig. 4, n+ heavily doped region 18b is situated inside the p+ heavily doped region 19

which is situated on the substrate 10. Another heavily doped n+ region is formed on the

substrate 10. The doped regions 18a, 18b and 19 are adjacent are situated on the source and

drain regions of the gate 17 and adjacent to each other via lightly doped region 13. Goo fails to

disclose the required plurality number of heavily doped regions. However, Guterman discloses a

high coupling ratio electrically programmable ROM where in Figs. 2 and 3, the required plurality

number of heavily doped regions are disclosed.

Allowable Subject Matter

1. Claims 6-11 allowed.

2. Claims 5 objected to as being dependent upon a rejected base claim, but would be

allowable if rewritten in independent form including all of the limitations of the base claim and

any intervening claims.

The following is a statement of reasons for the indication of allowable subject matter:

Prior art failed to establish the high density ROM structure with the required diode structure.

Claim Rejections - 35 USC § 103

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3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

- (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 4. Claims 1-4 and rejected under 35 U.S.C. 103(a) as being unpatentable over Goo (5,677,215) in view of Guterman (4,422,092)

Regarding Claims 1-4, Goo discloses a method of fabricating a nonvolatile semiconductor memory device where in Fig. 4, n+ heavily doped region 18b is situated inside the p+ heavily doped region 19 which is situated on the substrate 10. Another heavily doped n+ region is formed on the substrate 10. The doped regions 18a, 18b and 19 are adjacent are situated on the source and drain regions of the gate 17 and adjacent to each other via lightly doped region 13. Goo fails to disclose the required plurality number of heavily doped regions. However, Guterman discloses a high coupling ratio electrically programmable ROM where in Figs. 2 and 3, the required plurality number of heavily doped regions are disclosed.

It would have been obvious to one of having ordinary skill in the art at the time the invention was made to include the required plurality number of highly doped regions in Goo as taught by Guterman in order to have a ROM structure with better functionality.

Also regarding Claims 1-4, Chen et al. reference is included as related art.

Conclusion

5. THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Fazli Erdem whose telephone number is (571) 272-1914. The examiner can normally be reached on M - F 8:00 - 5:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (571) 272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

FE May 14, 2005

> NATHAN J. FLYNN SUPERVISORY PATENT EXAMINER TECHNOLOGY CENTER 2800